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Application No.: 09/990,397

Docket No.: JCLA7289

In The Specification:

Please amend paragraph [0023] and [0024] as follows:

[0023] High dielectric constant material is a term that refers to a dielectric constant

material that is greater than a Si₃N₄/SiO₂ (NO) dielectric constant material. High dielectric

constant layer 214 is made of a material, such as Al₂O₃, Y₂O₃, ZrSi_xO_y, HfSi_xO_y, La₂O₃, ZrO₂,

HfO₂, Ta₂O₅, Pr₂O₃ or TiO₂. Table 1 below indicates the dielectric constants in the above-

described dielectric layer, which furthermore includes the dielectric constants Si₃N₄/SiO₂, SiO₂

and Si₃N₄.

As indicated in Table 1, the dielectric constant of the high dielectric constant materials is usually

greater than the Si₃N₄/SiO₂ dielectric constant value of 8. The high dielectric constant dielectric

layer 214 in the present embodiment can also be an admixture of the above-mentioned high

dielectric constant materials or a stacked layer 214a of the above-mentioned high dielectric

constant materials, as shown in Fig. 3.

[0024] Moreover, whether or not to leave out the second oxide layer 216 between the

high dielectric constant dielectric layer 214 and the control gate 208 within the dielectric stacked

layer 210 is decided according to the band gap size of the high dielectric constant dielectric layer

214 used. If the band gap of the utilized high dielectric constant dielectric layer 214 is as wide or

is wider than the silicon oxide band gap, then the second oxide layer 216 is left out, as shown in

Fig. 4. The high dielectric constant dielectric layer 214 can be an admixture of the above-

mentioned high dielectric constant materials. It can also be a stacked layer 214a of the above-

mentioned high dielectric constant materials, as shown in Fig. 5. Alternately, if the band gap of

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the high dielectric constant dielectric layer 214 is less than he silicon oxide band gap, then the second oxide layer 216 is included. Table 2 below indicates the band gap values of the utilized dielectric layer 214 material in the present embodiment and furthermore includes the band gap values of SiO₂ and Si₃N₄.

In The Drawings:

Please substitute the attached drawing of Fig. 3-5 for showing every feature of the invention in the claims.